

ZXMN3A01F

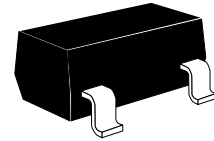
30V N-CANNEL ENHANCEMENT MODE MOSFET

SUMMARY

$V_{(BR)DSS} = 30V$; $R_{DS(ON)} = 0.12\Omega$ $I_D = 2.0A$

DESCRIPTION

This new generation of TRENCH MOSFETs from TY utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



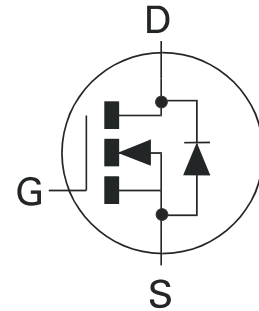
SOT23

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- SOT23 package

APPLICATIONS

- DC - DC Converters
- Power Management Functions
- Motor control

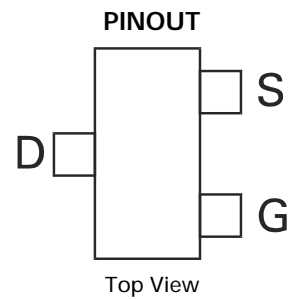


ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXMN3A01FTA	7"	8mm	3000 units
ZXMN3A01FTC	13"	8mm	10000 units

DEVICE MARKING

- 7N3



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ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DSS}	30	V
Gate Source Voltage	V _{GS}	±20	V
Continuous Drain Current V _{GS} =10V; T _A =25°C (b) V _{GS} =10V; T _A =70°C (b) V _{GS} =10V; T _A =25°C (a)	I _D	2.0 1.6 1.8	A
Pulsed Drain Current (c)	I _{DM}	8	A
Continuous Source Current (Body Diode) (b)	I _S	1.3	A
Pulsed Source Current (Body Diode) (c)	I _{SM}	8	A
Power Dissipation at T _A =25°C (a) Linear Derating Factor	P _D	625 5	mW mW/°C
Power Dissipation at T _A =25°C (b) Linear Derating Factor	P _D	806 6.4	mW mW/°C
Operating and Storage Temperature Range	T _j ;T _{stg}	-55 to +150	°C

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	R _{θJA}	200	°C/W
Junction to Ambient (b)	R _{θJA}	155	°C/W

NOTES

(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

(b) For a device surface mounted on FR4 PCB measured at t≤5 secs.

(c) Repetitive rating 25mm x 25mm FR4 PCB, D = 0.05, pulse width 10μs - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

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ELECTRICAL CHARACTERISTICS (at $T_A = 25^\circ\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	30			V	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}			0.5	μA	$V_{DS}=30\text{V}, V_{GS}=0\text{V}$
Gate-Body Leakage	I_{GSS}			100	nA	$V_{GS}=\pm 20\text{V}, V_{DS}=0\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	1			V	$I_D=250\mu\text{A}, V_{DS}=V_{GS}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		0.106	0.12 0.18	Ω Ω	$V_{GS}=10\text{V}, I_D=2.5\text{A}$ $V_{GS}=4.5\text{V}, I_D=2.0\text{A}$
Forward Transconductance (1)(3)	g_{fs}		3.5		S	$V_{DS}=4.5\text{V}, I_D=2.5\text{A}$
DYNAMIC (3)						
Input Capacitance	C_{iss}		190		pF	$V_{DS}=25\text{V}, V_{GS}=0\text{V},$ $f=1\text{MHz}$
Output Capacitance	C_{oss}		38		pF	
Reverse Transfer Capacitance	C_{rss}		20		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	$t_{d(on)}$		1.7		ns	$V_{DD}=15\text{V}, I_D=2.5\text{A}$ $R_G \cong 6.0\Omega, V_{GS}=10\text{V}$
Rise Time	t_r		2.3		ns	
Turn-Off Delay Time	$t_{d(off)}$		6.6		ns	
Fall Time	t_f		2.9		ns	
Gate Charge	Q_g		2.3		nC	$V_{DS}=15\text{V}, V_{GS}=5\text{V},$ $I_D=2.5\text{A}$
Total Gate Charge	Q_g		3.9		nC	$V_{DS}=15\text{V}, V_{GS}=10\text{V},$ $I_D=2.5\text{A}$
Gate-Source Charge	Q_{gs}		0.6		nC	
Gate-Drain Charge	Q_{gd}		0.9		nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V_{SD}		0.85	0.95	V	$T_J=25^\circ\text{C}, I_S=1.7\text{A},$ $V_{GS}=0\text{V}$
Reverse Recovery Time (3)	t_{rr}		17.7		ns	$T_J=25^\circ\text{C}, I_F=2.5\text{A},$ $di/dt=100\text{A}/\mu\text{s}$
Reverse Recovery Charge (3)	Q_{rr}		13.0		nC	

NOTES

- (1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$.
- (2) Switching characteristics are independent of operating junction temperature.
- (3) For design aid only, not subject to production testing.